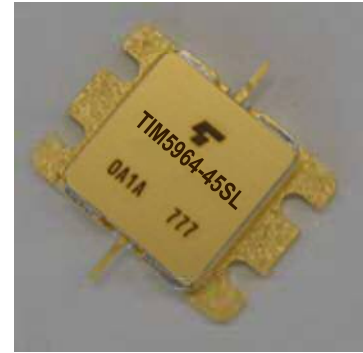


FEATURES

- **BROAD BAND INTERNALLY MATCHED FET**
- **HIGH POWER**
P1dB= 46.5dBm at 5.9GHz to 6.4GHz
- **HIGH GAIN**
G1dB= 9.0dB at 5.9GHz to 6.4GHz
- **LOW INTERMODULATION DISTORTION**
IM3= -42dBc(Min.) at Pout= 35.5dBm (Single Carrier Level)
- **HERMETICALLY SEALED PACKAGE**



RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 9.0A f= 5.9 to 6.4GHz	dBm	46.0	46.5	—
Power Gain at 1dB Gain Compression Point	G1dB		dB	8.0	9.0	—
Drain Current	IDS1		A	—	9.6	10.8
Gain Flatness	ΔG		dB	—	—	±0.8
Power Added Efficiency	ηadd		%	—	41	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 35.5dBm, Δf= 5MHz (Single Carrier Level)	dBc	-42	-45	—
Drain Current	IDS2		A	—	9.6	10.8
Channel Temperature Rise	ΔTch	(VDS × IDS + Pin - P1dB) × Rth(c-c)	°C	—	—	100

Recommended Gate Resistance(Rg): 28 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

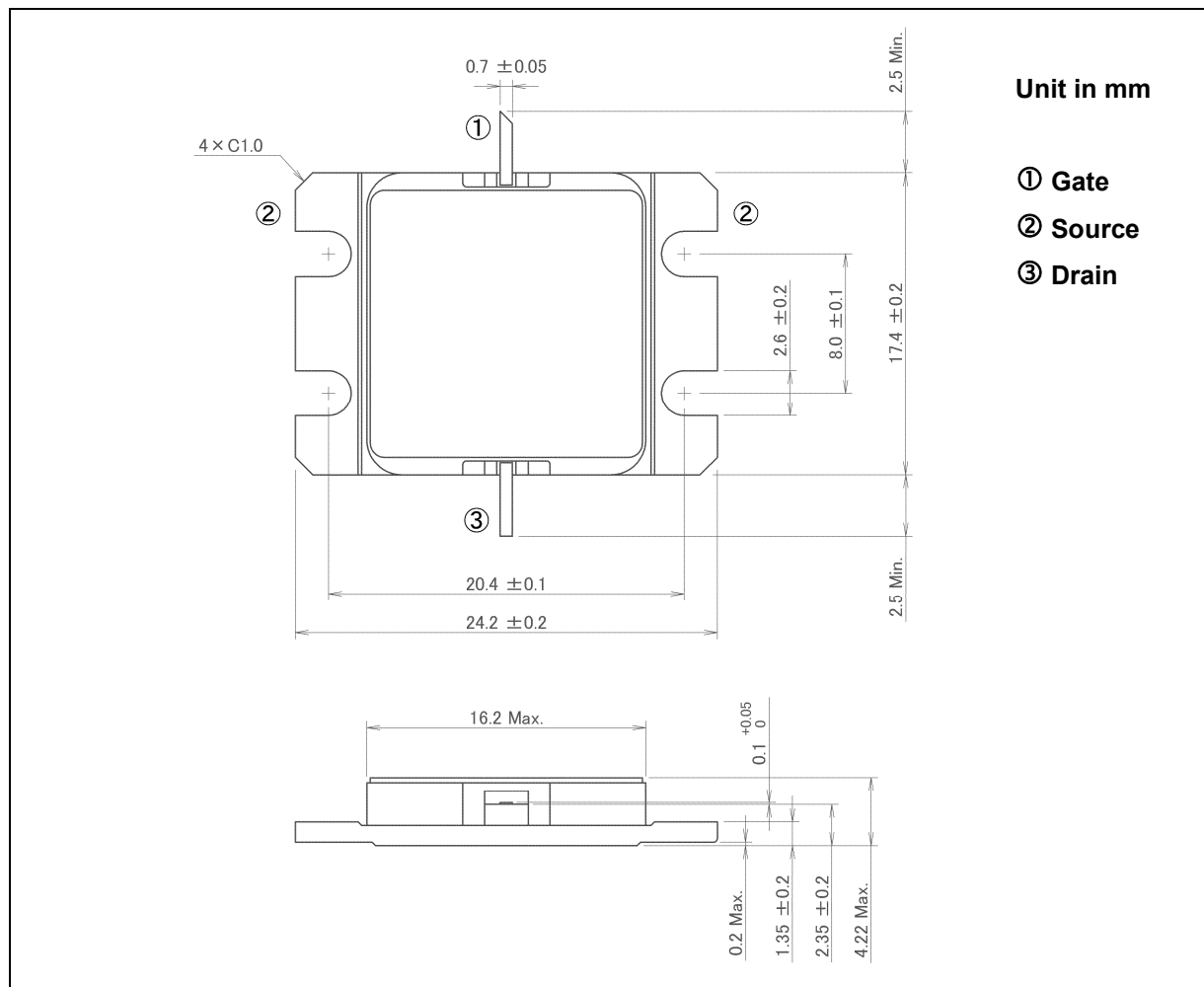
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 11.0A	S	—	8.0	—
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 170mA	V	-1.0	-2.5	-4.0
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	A	—	24	—
Gate-Source Breakdown Voltage	VGSO	IGS= -500μA	V	-5	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	0.8	1.2

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	A	20
Total Power Dissipation (Tc= 25°C)	PT	W	125
Channel Temperature	Tch	°C	175
Storage Temperature	Tstg	°C	-65 to +175

PACKAGE OUTLINE (2-16G1B)



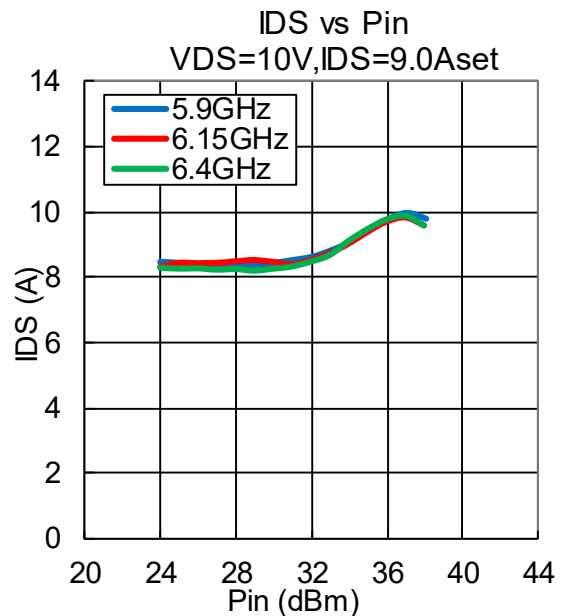
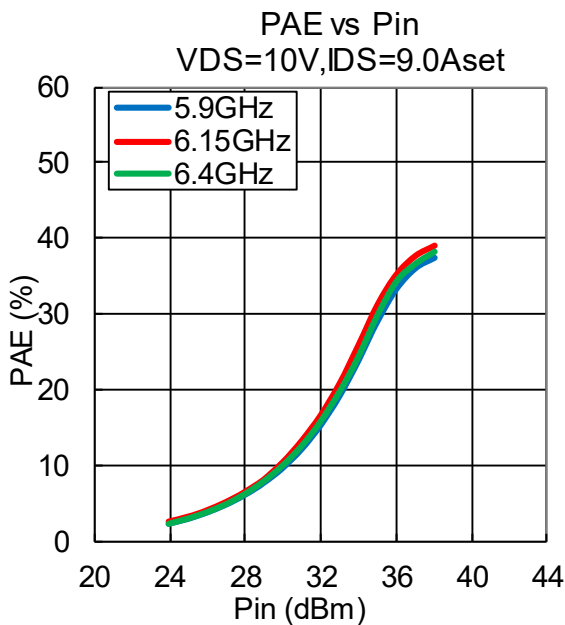
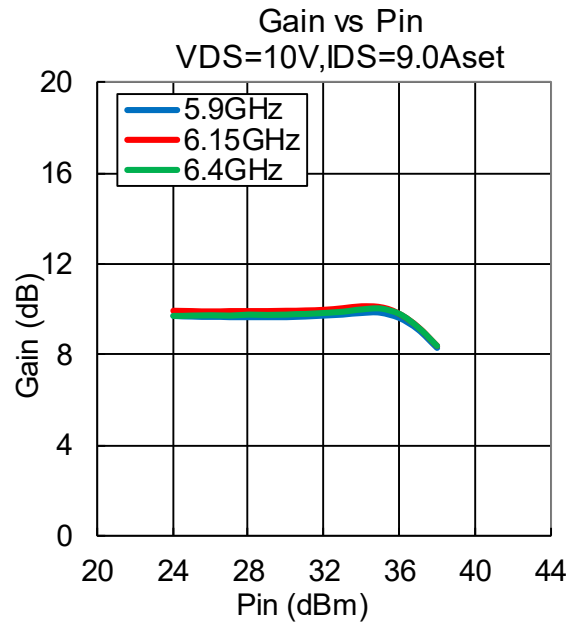
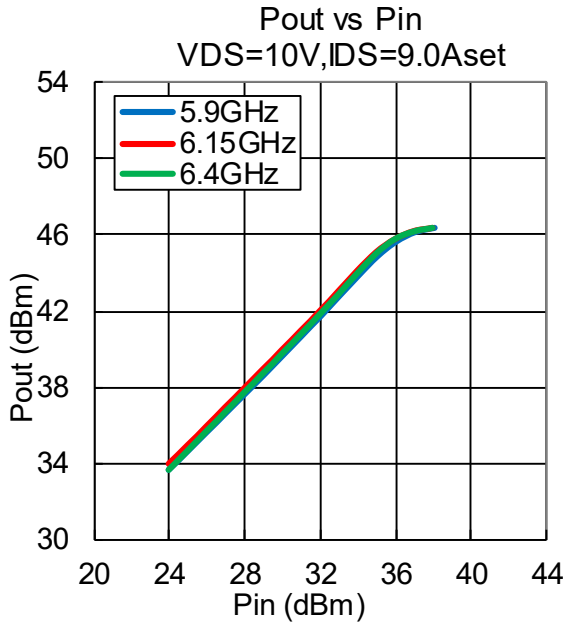
HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

TYPICAL RF PERFORMANCE

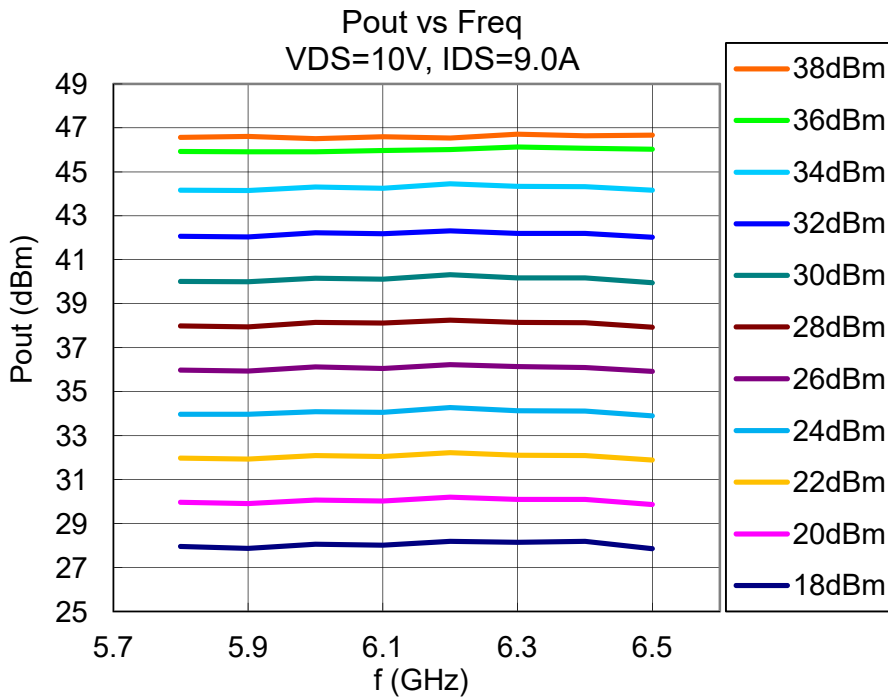
•Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 9 A, f= 5.9, 6.15, 6.4 GHz, Ta= +25 °C



·Pout vs. Frequency

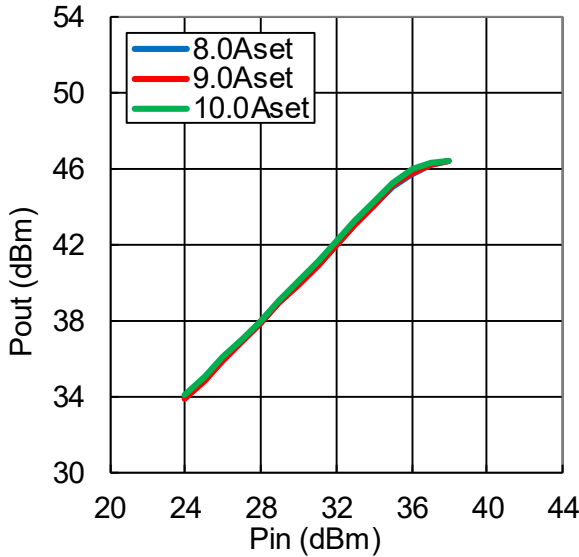
VDS= 10 V, IDSset= 9.0 A, Ta= +25 °C



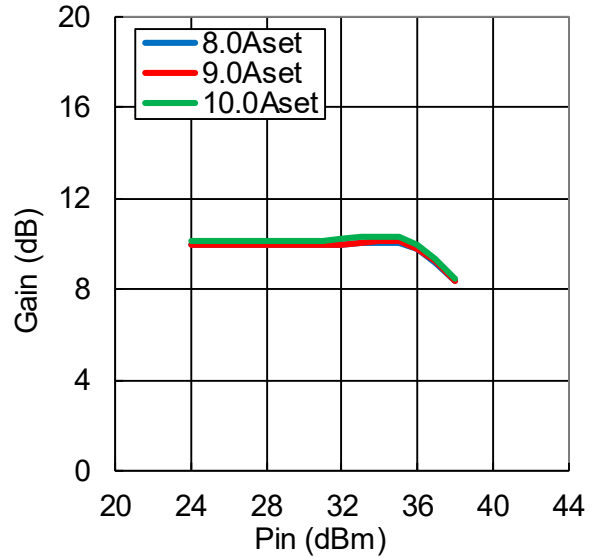
•Pout , Gain , PAE , IDS vs. Pin vs. IDSset

VDS= 10 V, IDSset= 8.0, 9.0, 10.0 A, f= 6.15 GHz, Ta= +25 °C

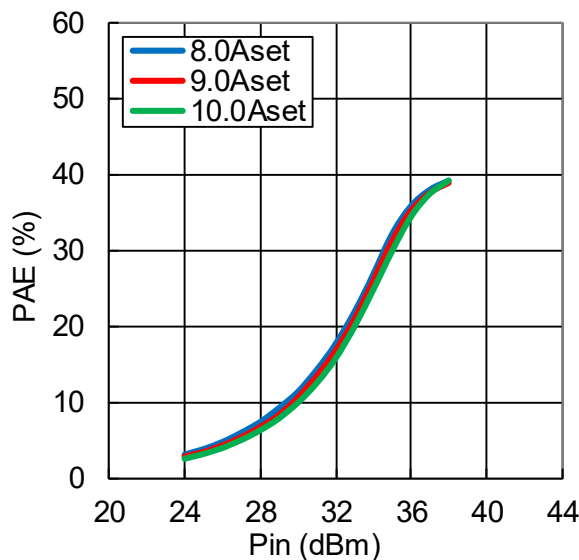
Pout vs Pin
VDS=10V,f=6.15GHz



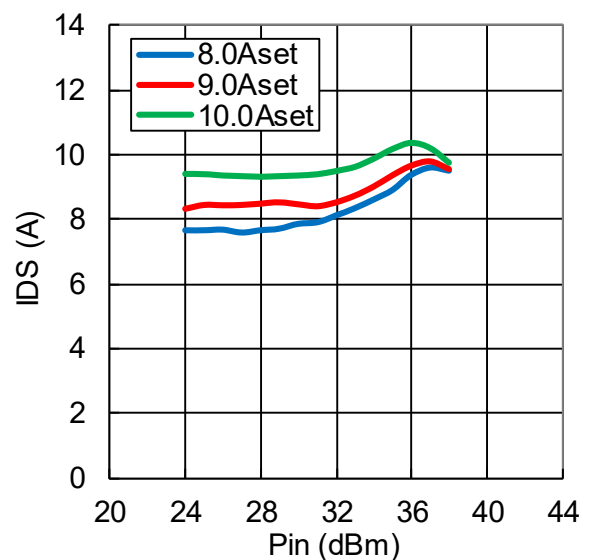
Gain vs Pin
VDS=10V,f=6.15GHz



PAE vs Pin
VDS=10V,f=6.15GHz

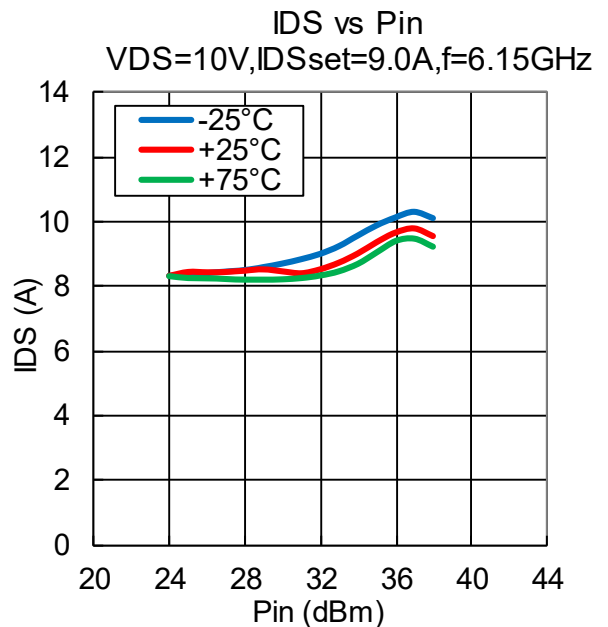
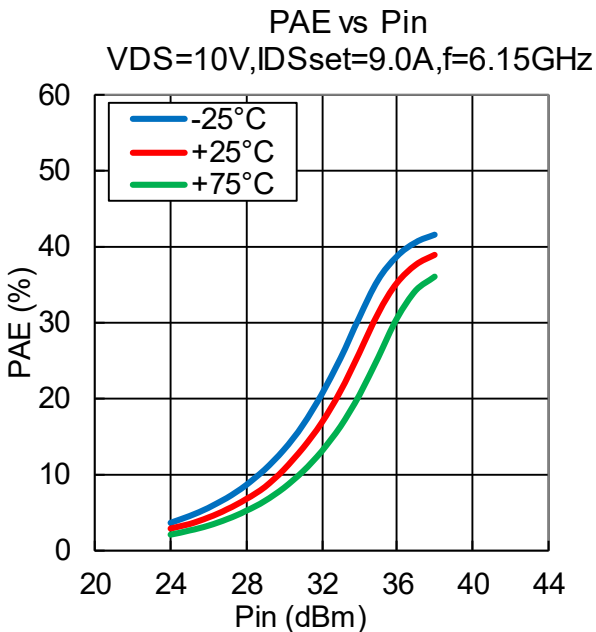
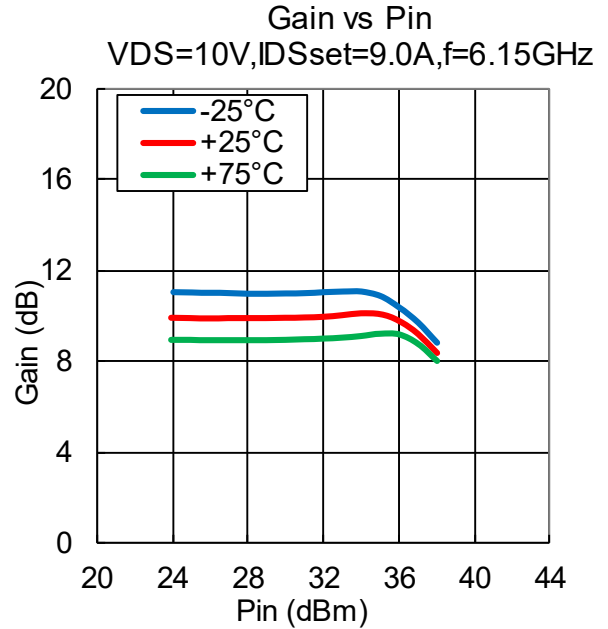
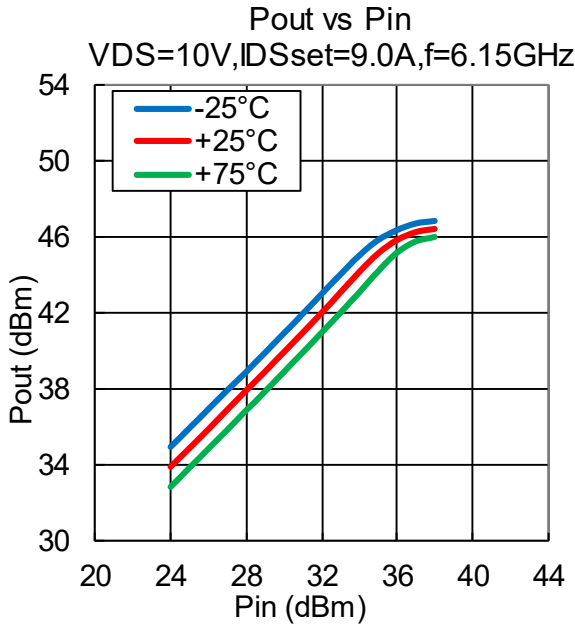


IDS vs Pin
VDS=10V,f=6.15GHz



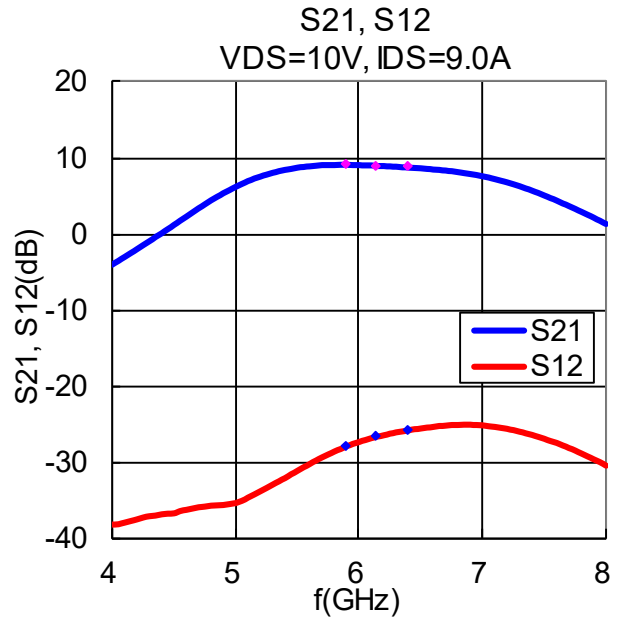
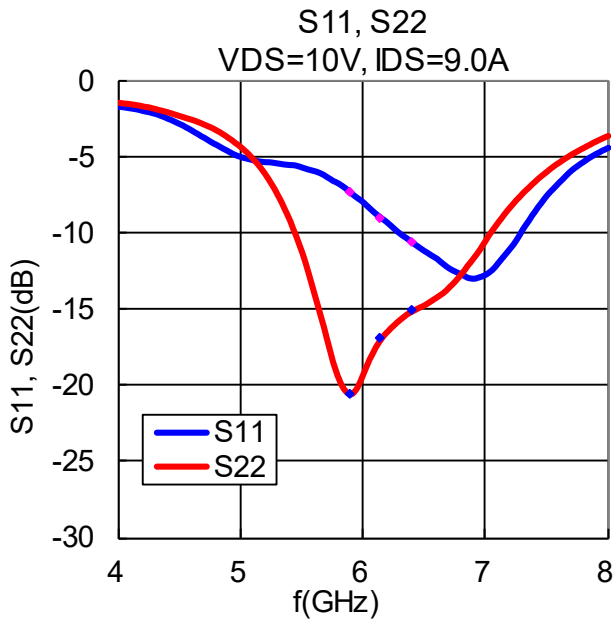
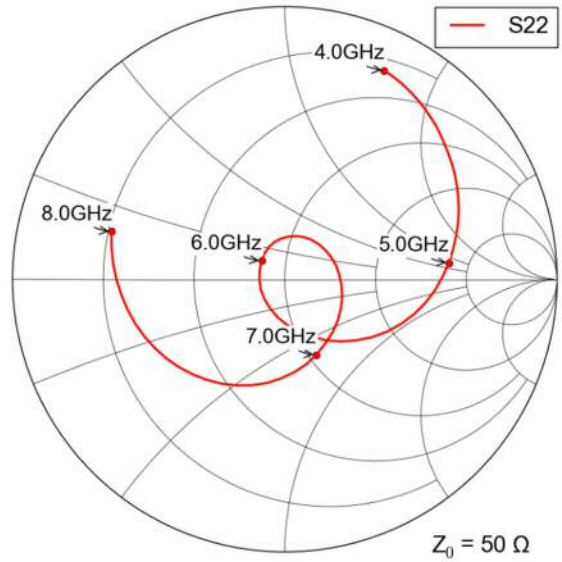
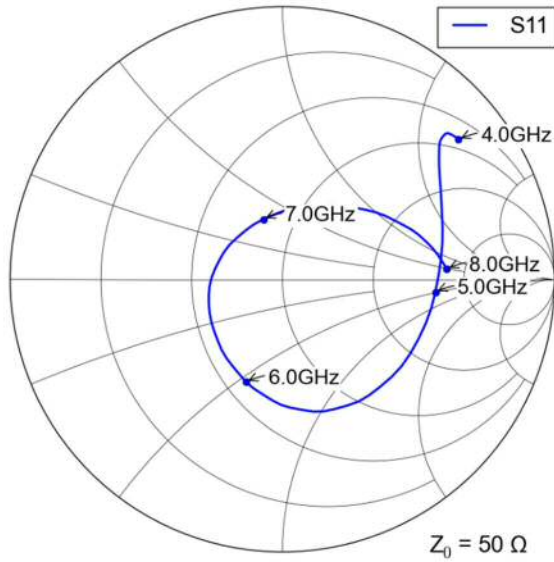
-Pout , Gain , PAE , IDS vs. Pin vs. Temperature

VDS= 10 V, IDSset= 9.0 A, f= 6.15 GHz, Ta= -25, +25, +75 °C



-S-Parameters

VDS= 10 V, IDSset= 9.0 A, f= 4.0 to 8.0 GHz, Ta= +25 °C



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